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October 2013

FQB50N06 / FQI50N06 N-Channel QFET® MOSFET

60 V, 50 A, 22 mΩ

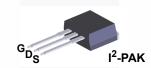
Description

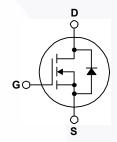
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 50 A , 60 V, $R_{DS(on)}$ = 22 m Ω (Max.) @V_{GS} = 10 V, I_D = 25 A
- Low Gate Charge (Typ. 31 nC)
- Low Crss Typ. 65 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating







Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQB50N06TM / FQI50N06TU	Unit
V_{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous (T _C = 25°C)		50	Α
	- Continuous (T _C = 100°C)		35.4	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	200	Α
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	490	mJ
I _{AR}	Avalanche Current	(Note 1)	50	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
P_{D}	Power Dissipation (T _A = 25°C) *		3.75	W
	Power Dissipation (T _C = 25°C)		120	W
	- Derate above 25°C		0.8	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQB50N06TM FQI50N06TU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 1.24		
В	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (* 1 in² pad of 2 oz copper), Max.	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity	
FQB50N06	FQB50N06TM	D2-PAK	330mm	24mm	800	
FQI50N06	FQI50N06TU	I2-PAK	-	-	50	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to 25°C		0.06		V/°(
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V			1	μΑ
		V _{DS} = 48 V, T _C = 150°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 25 \text{ A}$		0.018	0.022	Ω
g _{FS}	Forward Transconductance	V _{DS} = 25 V, I _D = 25 A		22		S
C _{oss}	Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		440 65	580 90	pF pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 30 V, I _D = 25 A,		15	40	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$	/	105	220	ns
t _{d(off)}	Turn-Off Delay Time			60	130	ns
t _f	Turn-Off Fall Time	(Note 4)	/	65	140	ns
Qg	Total Gate Charge	V _{DS} = 48 V, I _D = 50 A,		31	41	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		8		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		13		nC
Drain-S	Source Diode Characteristics at	nd Maximum Ratings				
I _S	Source Diode Characteristics and Maximum Ratings Maximum Continuous Drain-Source Diode Forward Current				50	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			200	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 50 \text{ A}$			1.5	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = 50 \text{ A},$		52		ns
Q _{rr}	Reverse Recovery Charge	dl _F / dt = 100 A/μs		75		nC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 230μH, I_{AS} = 50A, V_{DD} = 25V, R_G = 25 Ω , Starting T_J = 25°C 3. I_{SD} \leq 50A, di/dt \leq 300A/μs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C 4. Essentially independent of operating temperature

Typical Characteristics

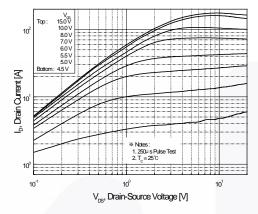


Figure 1. On-Region Characteristics

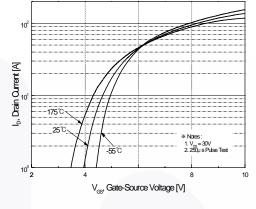


Figure 2. Transfer Characteristics

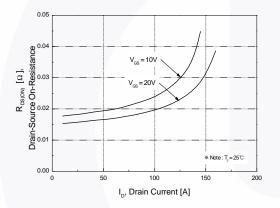


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

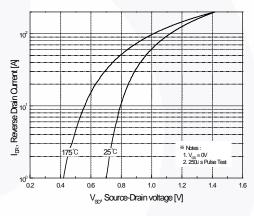


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

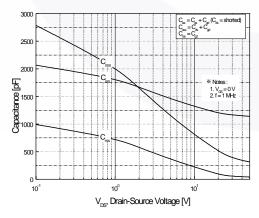


Figure 5. Capacitance Characteristics

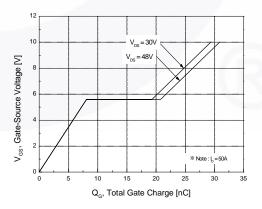


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

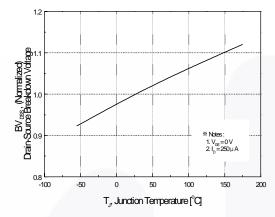


Figure 7. Breakdown Voltage Variation vs. Temperature

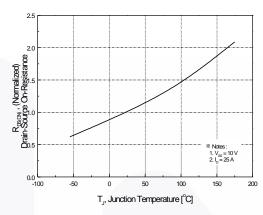


Figure 8. On-Resistance Variation vs. Temperature

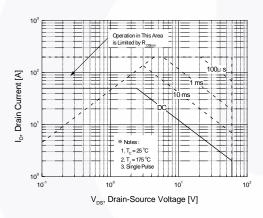


Figure 9. Maximum Safe Operating Area

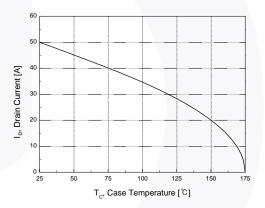


Figure 10. Maximum Drain Current vs. Case Temperature

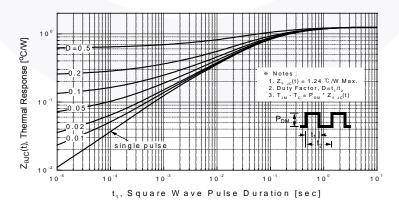


Figure 11. Transient Thermal Response Curve



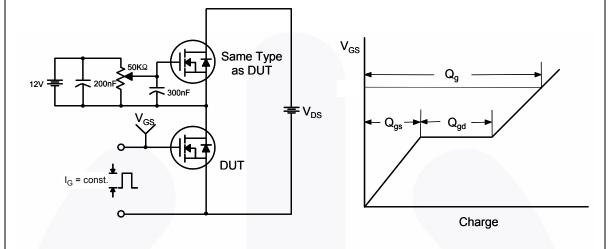


Figure 13. Resistive Switching Test Circuit & Waveforms

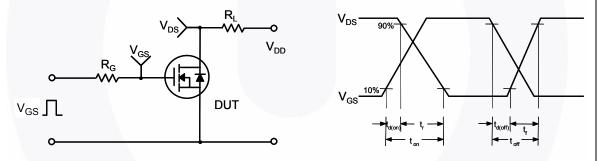
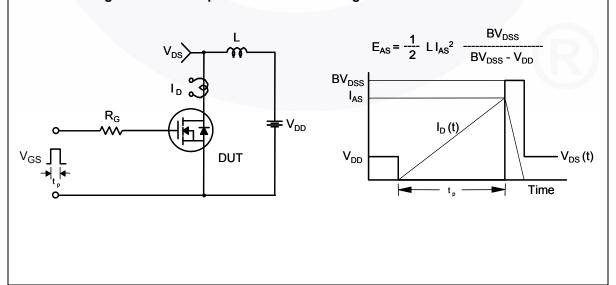
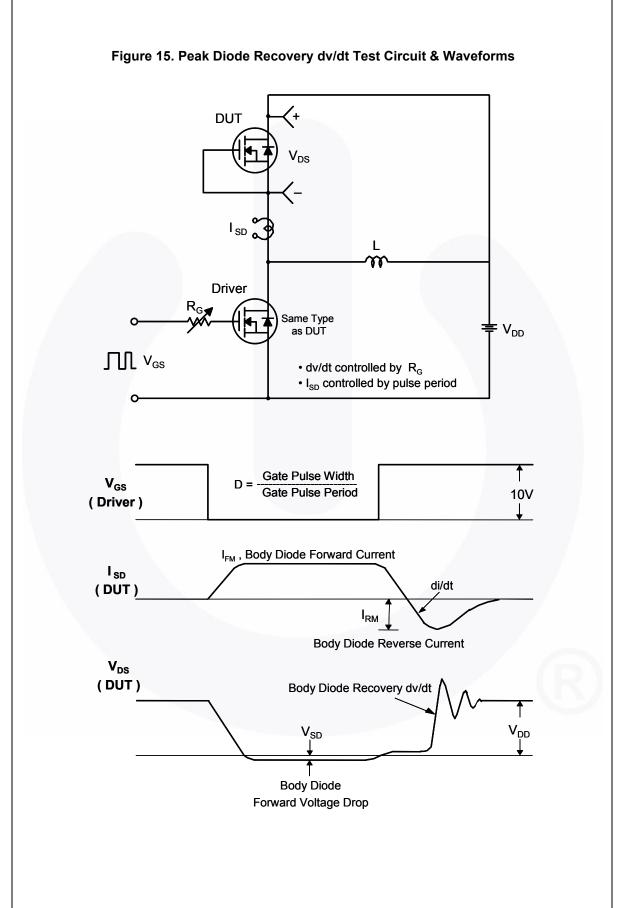


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





Mechanical Dimensions

TO-263 2L (D²PAK)

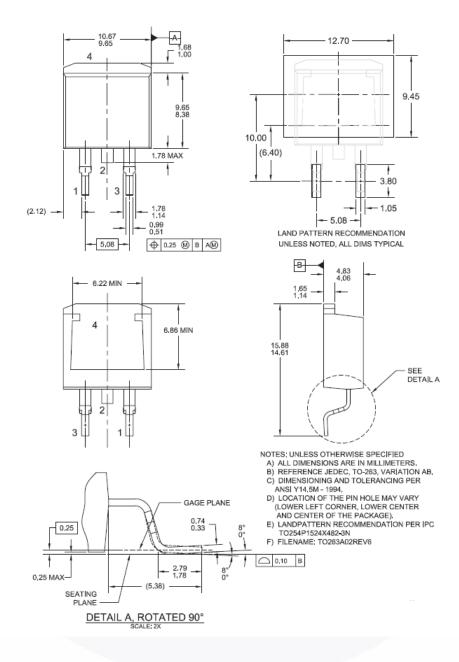


Figure 16. 2LD, TO263, Surface Mount

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http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT263-002

Dimension in Millimeters

Mechanical Dimensions

TO-262 3L (I²PAK)

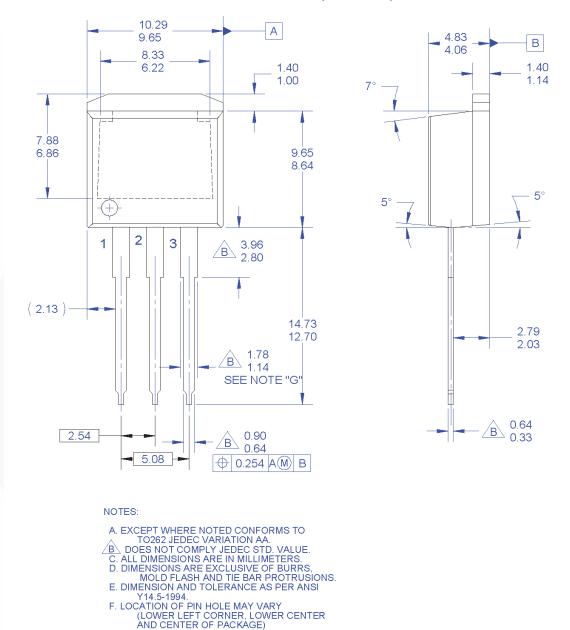


Figure 17. 3LD, TO262, Jedec Variation AA (12PAK)

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G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX. H. DRAWING FILE NAME: TO262A03REV5

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Dimension in Millimeters





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